

AMENDMENTS TO THE CLAIMS

The below listing of claims replaces all prior versions of claims in the application.

1. (Previously Presented) A semiconductor device fabrication method comprising:

a first polishing of polishing a surface of a film-to-be-polished while a polishing slurry including abrasive grains and a surfactant is supplied onto a polishing pad through a first nozzle;
and

a second polishing of polishing the surface of the film-to-be-polished while said polishing slurry is supplied onto a polishing pad through the first nozzle and water is further supplied onto the polishing pad through a second nozzle different from the first nozzle,

wherein supply of said water through the second nozzle starts at the second polishing after the first polishing.

2. (Cancelled)

3. (Currently Amended) A semiconductor device fabrication method according to claim 1, wherein

in the second polishing, said water is supplied to ~~a position outer of a position for said polishing slurry to be supplied to~~ first position on a polishing table, and the polishing slurry is supplied to a second position on the polishing table,

wherein a distance between the first position and a center position of the polishing table is larger than a distance between the center position and the second position.

4. (Previously Presented) A semiconductor device fabrication method according to claim 1, wherein

in the second polishing, a supply amount of said water is 2 or more times as much as a supply amount of said polishing slurry.

5. - 11. (Cancelled)

12. (Previously Presented) A semiconductor device fabrication method according to claim 1, further comprising, before the first polishing:

forming over a semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,

in the second polishing, the surface of the film-to-be-polished is polished with the insulation film as a stopper.

13. - 27. (Cancelled)

28. (Previously Presented) A semiconductor device fabrication method according to claim 1, wherein

the abrasive grains comprise cerium oxide or silicon oxide,

the surfactant comprises poly(ammonium acrylate).

29. - 33. (Cancelled)

34. (Previously Presented) A semiconductor device fabrication method according to claim 1, wherein

in the second polishing, a supply amount of said polishing slurry to a supply amount of said water is 1:5.

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35. (Previously Presented) A semiconductor device fabrication method according to claim 1, wherein the polishing pad used in the second polishing is different from the polishing pad used in the first polishing.

36. (Cancelled)